

Abstract of the Disclosure:

The apparatus allows monitoring layer depositions in a process chamber. The apparatus has a light source, a sensor element, and at least one light detector. The sensor element is  
5 suitably configured in order to influence the intensity of the light beam measured by the detector by the thickness of the layer growing on the sensor element. The novel monitoring method for measuring the transmitted light intensity utilizes the apparatus. The sensor element has a continuous opening  
10 through which the intensity of the light is observed as a function of the opening grown over by the thickness of the growing layer.

10033950-122801

WHS:tk-1999P8173F//12/27/2001